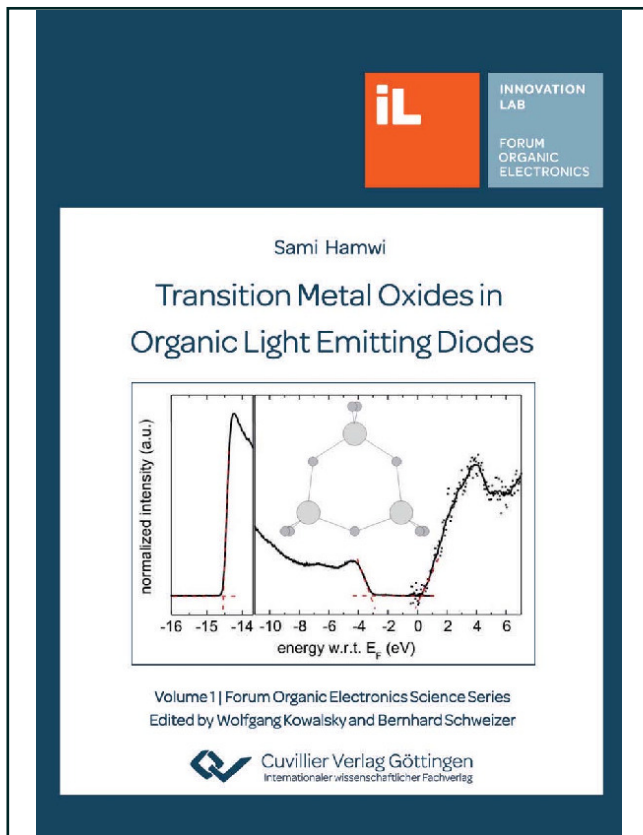




Sami Hamwi (Autor)

## Transition Metal Oxides in Organic Light Emitting Diodes



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